

IDS - 07/13/2006

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Complete If Known	
		Application Number	10/860,048
		Filing Date	September 11, 2003
		First Named Inventor	Lanzerotti, et al.
		Group Art Unit	2826
		Examiner Name	Quach, Tuan N.
Sheet 1	of 1	Attorney Docket Number	BUR920010146US2

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
TQ		5,734,183		Morishita	03/31/1998	
TQ		6,246,104 B1		Tsuda, et al.	06/12/2001	

U.S. PATENT PUBLICATIONS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
TQ		2002/0192918 A1		Takagi, et al.	12/19/2002	
TQ		2003/0006484 A1		Asai, et al.	01/09/2003	
TQ		2003/0094673 A1		Dunn, et al.	05/22/2003	
TQ		2004/0251473 A1		Asai, et al.	12/16/2004	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Number			Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number	Kind Code ⁵ (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²

Examiner Signature	/Tuan Quach/	Date Considered	08/19/06
-----------------------	--------------	--------------------	----------

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. BUR920010146US2		SERIAL NO. 10/660,048 Not Yet Assigned	
				Lanzerotti et al.			
				FILING Concurrently Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TQ		4,885,614	12/05/1989	Furukawa et al.	_____	_____	
		5,116,455	05/26/1992	Daly	_____	_____	
		5,321,302	06/14/1994	Shimawaki	_____	_____	
		5,338,945	08/16/1994	Baliga et al.	_____	_____	
		5,360,986	11/01/1994	Candelaria	_____	_____	
		5,404,028	04/04/1995	Metzger et al.	_____	_____	
		5,468,658	11/21/1995	Bayraktaroglu	_____	_____	
		5,557,118	09/17/1996	Hashimoto	_____	_____	
		5,731,626	03/24/1998	Eaglesham et al.	_____	_____	
		5,783,845	07/21/1998	Kondo et al.	_____	_____	
TQ		5,986,287	11/16/1999	Eberl et al.	_____	_____	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TQ		JP11312685A	11/09/1999	Japan w/Abstract	_____	_____	
		JP2000012558A	01/14/2000	Japan w/Abstract	_____	_____	
		JP92000174033A	06/23/2000	Japan w/Abstract	_____	_____	
TQ		WO 98/26457	06/18/1998	Germany	_____	_____	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
TQ		Lanzerotti et al., "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", 1996 IEEE, pp. 10.2.1 - 10.2.4					
TQ		Stock et al. "Carbon Incorporation in Silicon for Suppressing Interstitial-Enhanced Boron Diffusion", Applied Physics Letter, March 13, 1995, Vol. 66, Issue 11, pp. 1370-1372					
EXAMINER /Tuan Quach/				DATE CONSIDERED 08/21/2006			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.
BUR920010146US2

SERIAL NO. 10/660,048
Not Yet Assigned

Lanzerotti et al.

FILING
Concurrently Herewith

GROUP
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TQ	6,043,139	03/28/2000	Eaglesham et al.			
	6,096,617	08/01/2000	Kizuki			
	6,107,151	08/22/2000	Enquist			
	6,229,197	05/08/2001	Plumton et al.			
	6,534,371	03/2003	Coolbaugh et al.			
	6,509,242	01/2003	Frei et al.			
	5,814,843	09/1998	Ohkubo, Michio			
TQ	5,387,807	02/1995	Bayraktaroglu, Burhan			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TQ		Ghanti et al., "Control of Implant-Damage-Enhanced Boron Diffusion in Epitaxially Grown Si/p-Siz-x Gex/n-Si Heterojunction Bipolar Transistors", Journal of Electronic Materials, Vol. 24, No. 8, 1995, pp. 999-1002
TQ		Bodnar et al., "Growth of Ternary Alloy Siz-x-yGexCy By Rapid Thermal Chemical Vapor Deposition", Journal Vac. Science Technology, A., Vol. 1. 13, N. 5, Sept/Oct. 1995, pp.2336-2340

EXAMINER

/Tuan Quach/

DATE CONSIDERED

08/21/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw lin through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
BUR920010146US2

SERIAL NO. 10/660,048
Not Yet Assigned

Lanzerotti et al.

FILING
Concurrently Herewith

GROUP
Unknown

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TQ		Regolini et al., "Growth and Characterization of Strain Compensated Siz-x-yGexCy Epitaxial Layers", Materials Letters 18, 1993, pp. 57-60
TQ		Lanzerotti et al., "Si/Siz-x-yGexCy/Si Heterojunction Bipolar Transistors", IEEE Electronic Device Letters, Vol. 17, No. 7, July 1996, pp. 334-337

EXAMINER /Tuan Quach/

DATE CONSIDERED 08/21/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.
BUR920010146US2

SERIAL NO. 10/660,048
Not Yet Assigned

Lanzerotti et al.

FILING
Concurrently Herewith

GROUP
Unknown

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TQ			Poate et al., "Ion Implantation and Transient Enhanced Diffusion", IEDM 95-77, IEEE 1995, pp. 4.1.1 - 4.1.4

EXAMINER

/Tuan Quach/

DATE CONSIDERED

08/21/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.